


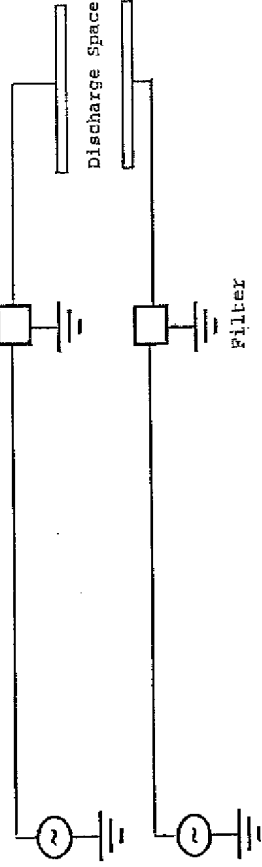

Correspondence Table 1-1

	The present Application	Priority Document JP2003-197799
Claims 1-3	an atmospheric pressure plasma processing apparatus at atmospheric pressure or at approximately	[0001], [0022]
	(i) high frequency electric field A is formed by superposing a first high frequency electric field and a second high frequency electric field	Claim 7, [0007], [0027], [0035] - [0041]
	(i) a first high frequency electric field of 200 kHz or less and a second high frequency electric field of 800 kHz or more	[0039] - [0040]
	(ii) transferring energy of the excited discharge gas to a film forming gas, whereby the film forming gas is excited;	[0023]
	the first process comprising the steps of: (iii) exposing a substrate to the excited film forming gas, whereby a film is formed on the substrate,	Claim 1 [0014] - [0015]
	the second process comprising the steps of: (v) exposing the film formed in the first process to the excited gas containing the oxidizing gas,	Example 1 [0056] - [0058]
	moving the substrate between the first discharge space and the second discharge space	Claim 2, [0032], FIG.1, FIG.2
	the discharge gas contains nitrogen of which content is 50 % by volume or more based on a volume of the discharge gas	Example 1 [0057], Example 2 [0072] film forming gas: 11 (=10+1) L/minute (21.1%) discharge gas: nitrogen 40 L/minute (76.9%)
	a discharge space of the first process is formed between a first electrode and a second electrode which are facing each other;	[0007], [0031], FIG. 1, FIG. 2, FIG. 3
	the first high frequency electric field is applied by the first electrode and the second high frequency electric field is applied by the second electrode	[0037], FIG. 2
Claim 4	the discharge gas contains a reducing gas	Example 1 [0057], Example 2 [0072] reducing gas: hydrogen 1 L/minute ( 1.9%)
Claim 5	the reducing gas is hydrogen	Example 1 [0057], Example 2 [0072]

Correspondence Table 1-2

	The present Application	Priority Document JP2003-197799
Claim 12	the film is a metal oxide film	Example 1 [0057], Example 2 [0072]
Claim 13	the film is a transparent conductive film	Example 1, [0069], Table 2, Example 2 [0072]
Claim 14	the film forming gas contains an organo-metallic compound having a metal atom selected from the group consisting of indium(In), tin(Sn), zinc(Zn), zirconium(Zr), antimony(Sb), aluminum(Al), gallium(Ga) and germanium(Ge)	Example 1 [0057], Example 2 [0072] In, Sn
Claim 15	the first process and the second process are alternately repeated a plurality of times	Claim 2, Example 1 [0058]
Claim 16	a thickness of the accumulated film in the first process per batch is not more than 10 nm	Claim 4, [0018], Example 1 [0058] - [0063]
Figures	FIG. 1	FIG. 1 + FIG. 2
	FIG. 2(a), FIG. 2(b)	FIG. 3(a), FIG. 3(b)

Comparison between the Present Application and Suemasa Reference

	Pressure	Gas	Applied Wave Form	Power Supply Mechanism	Electric Field in Discharge Space
Present Application Id 10/544,084	At or near atmospheric pressure (20 - 110 kPa)	Discharge Gas: Nitrogen > 50 volume %			
Reference Suemasa 6,089,181	Reduced pressure atmosphere (ex. 20 mTorr)	Gas: C4F8	